

MJE13002H6 (3DD13002H6)

硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

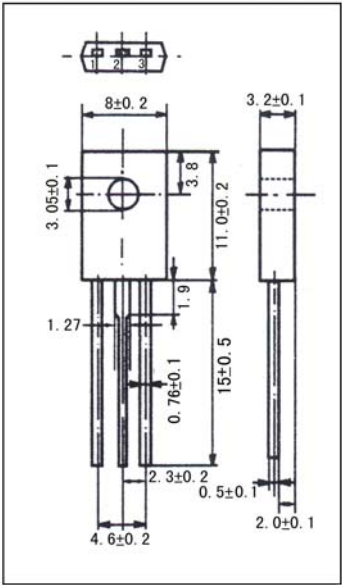
用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V_{CB0}	600	V
V_{CE0}	400	V
V_{EB0}	9.0	V
I_C	1.2	A
$P_c(T_a=25^{\circ}C)$	1.25	W
$P_c(T_c=25^{\circ}C)$	40	W
T_j	150	℃
T_{stg}	-55~150	℃

T0-126F反 单位: mm



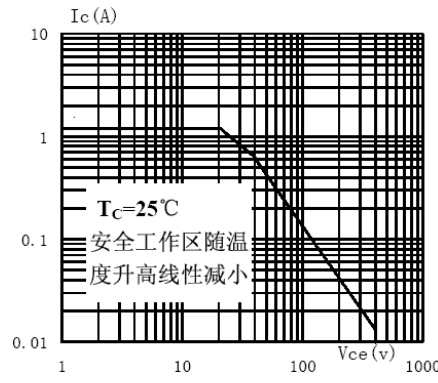
引脚： 1.B 2.C 3.E

电性能参数/Electrical characteristics(Ta=25℃)

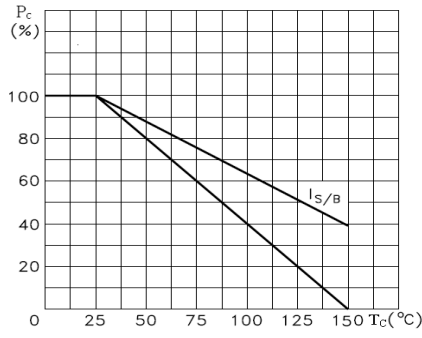
参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V_{CB0}	$I_C=1mA$ $I_E=0$	600			V
V_{CE0}	$I_C=10mA$ $I_B=0$	400			V
V_{EB0}	$I_E=1mA$ $I_C=0$	9.0			V
I_{CB0}	$V_{CB}=600V$ $I_E=0$			0.1	mA
I_{CE0}	$V_{CE}=400V$ $I_B=0$			0.1	mA
I_{EB0}	$V_{EB}=9.0V$ $I_C=0$			0.1	mA
h_{FE}	$V_{CE}=5.0V$ $I_C=200mA$	10		40	
$V_{CE(sat)}$	$I_C=500mA$ $I_B=100mA$			0.8	V
$V_{BE(sat)}$	$I_C=500mA$ $I_B=100mA$			1.2	V
f_T	$V_{CE}=10V$ $I_C=100mA$ $f=1.0MHz$	5.0			MHz
t_f	$V_{CE}=5V$ $I_C=250mA$ (UI9600)			0.6	μs
t_s				3.5	μs

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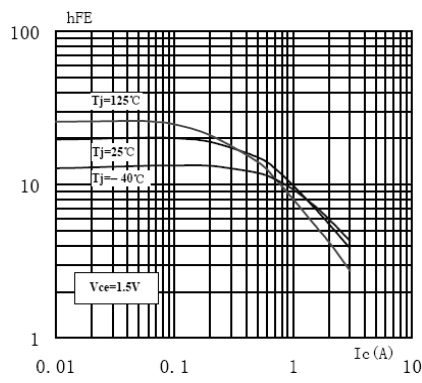
SOA (DC)



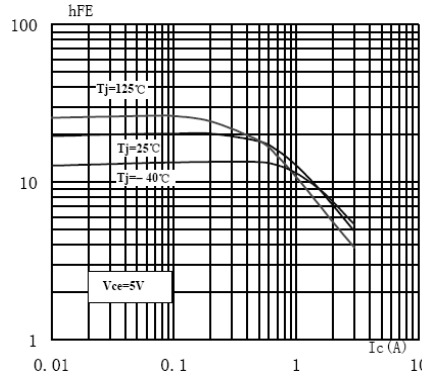
Pc-Tc



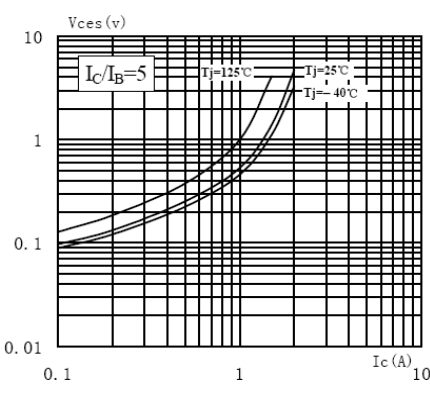
hFE-Ic



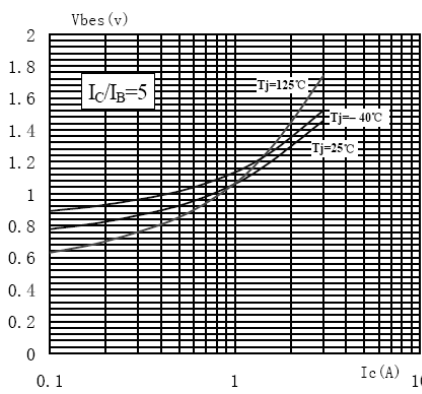
hFE-Ic



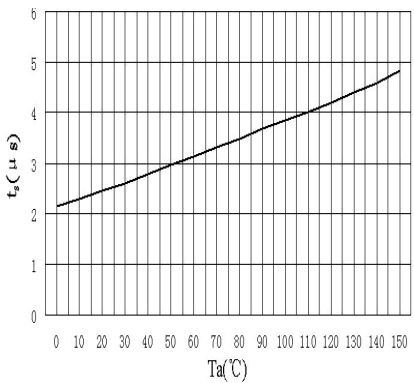
Vces-Ic



Vbes-Ic



ts-Ta



hFE-Ta

